

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Kazuhiro AIHARA, et al.

Serial No.: 09/499,037

Group Art Unit: 2826

Filed: February 07, 2000

Examiner: J. Mondt

For:

SEMICONDUCTOR DEVICE AND MANUFACTURING METHOD THEREOF

THE COMMISSIONER FOR PATENTS AND TRADEMARKS Washington, DC 20231

Dear Sir:

Transmitted herewith is an Amendment in the above identified application.

No additional fee is required.

Small entity status of this application under 37 CFR 1.9 and 1.27 has been established by a verified

statement previously submitted.

A verified statement to establish small entity status under 37 CFR 1.9 and 1.27 is enclosed.

Also attached:

The fee has been calculated as shown below:

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	NO. OF CLAIMS	HIGHEST PREVIOUSLY PAID FOR	EXTRA CLAIMS	RATE	FEE
Total Claims	6	20	0	\$18.00 =	\$0.00
Independent Claims	3	3	0	\$84.00 =	\$0.00
		Multiple claims newly presented			\$0.00
		Fee for extension of time			\$0.00
					\$0.00
Total of Above Calculations				\$0.00	

Please charge my Deposit Account No. <u>500417</u> in the amount of \$0.00. An additional copy of this transmittal sheet is submitted herewith.

The Commissioner is hereby authorized to charge payment of any fees associated with this communication or credit any overpayment, to Deposit Account No. 500417, including any filing fees under 37 CFR 1.16 for presentation of extra claims and any patent application processing fees under 37 CFR 1.17.

Respectfully submitted,

MCDERMOTT, WILL & EMERY

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PATENT

In re Application of

Kazuhiro AIHARA, et al.

Application No.: 09/499,037

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Group Art Unit: 2826

Examiner: J. Mondt

For: SEMICONDUCTOR DEVICE AND MANUFACTURING METHOD THEREOF

AMENDMENT

Box Non-Fee Amendment The Commissioner for Patents and Trademarks Washington, DC 20231

Sir:

The following Amendment and Remarks are submitted in response to the Office Action dated August 29, 2001. Please amend the above-identified application as follows:

IN THE CLAIMS:

Please amend claims 2-6 as follows:

2. (Amended) A semiconductor device, comprising:

a storage electrode including a tantalum nitride film formed over a semiconductor

substrate;

a capacitor dielectric film including a tantalum oxide film formed on and contacting an upper surface of said tantalum nitride film; and